Perovskite solar cells with NiO_x hole-transport layer

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Inverted perovskite solar cells (PSCs) have attracted interest due to their simple fabrication, long-term stability, and small hysteresis^[1-3]. It is noteworthy that the quality of the hole-transport layer (HTL) largely determines the device performance. Nickel oxide (NiO_x) has been paid great attention as a hole-transport material in PSCs because of its natural p-type property, low cost, good stability, and high transmittance^[4, 5]. Further, NiO_x has a suitable bandgap ($E_g > 3.50$ eV) and a well-matched valence band with perovskites, which is conducive to hole collection and electron blocking^[6, 7]. NiO_xbased inverted PSCs are promising for flexible and tandem solar cells due to their negligible hysteresis and low processing temperatures compatible with flexible substrates. Thus, more investigations into surface/interface modification, bandgap alignment, and the physical principles are worth paying effort to enhance device performance further.

Sol-gel method is mainly used to prepare Ni(OH)₂ by reacting Ni(NO₃)₂ with NaOH and then calcination to obtain NiO_x nanoparticles (Fig. 1(a))^[8]. However, NO_3^- as residue cannot be removed by subsequent process. They will be embedded in Ni(OH)₂, thus reducing the efficiency and long-term stability of the device. These ions can be removed at high temperatures, but this will lead to poor dispersion of the generated NiO_v in solution, seriously affecting the guality of the subsequent NiO_x HTL. In addition, NiO_x has a relatively low inherent conductivity, which limits the efficiency enhancement of PSCs^[9]. At the interface, organoiodide in perovskite can react with Ni^{3+} in NiO_x layer, and this reaction can affect the device stability. As shown in Fig. 1(b), there are three reactions at the interface^[10]: (1) Oxidation and deprotonation reactions generate iodine vapor and free protons; (2) the formation of volatile products at high temperatures, including hydrogen cyanide (HCN), methyliodide (CH₃I) and ammonia (NH₃); (3) with the increase of vapor pressure of free FA and MA molecules, the condensation product N-methyl formamidine can be formed. Therefore, to enhance the intrinsic stability and mobility is necessary for improving the device performance.

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Recently, doping ions have become an important strategy for improving NiO_x conductivity. To increase hole concentration, it is preferred to dope metal cations into NiO_x as acceptors. Doping metal ions like Li+[11], Cs+[12], Ag+[13], Cu2+[14], Sr^{2+[15]}, Co^{2+[6]}, Zn^{2+[16]}, rare earth ions^[17] or Pb²⁺/Li^{+[18]} can effectively improve NiO_x conductivity. Chen et al. doped Cs⁺ into NiO_x to increase conductivity and workfunction, resulting in a significant improvement in efficiency and stability^[12]. Doping bivalent metal cations with the same valence state as Ni can improve the mobility of NiO_x and device efficiency. Fig. 2(a) shows that the ionic radii of common bivalent metal cations mismatch with Ni ion radius within 10%, which can effectively promote the occurrence of substitution^[19]. Dong et al. used KBr as a buffer layer between the perovskite and NiO_x to improve the valence band maximum of NiO_x to -5.37 eV, which matches better with perovskite and facilitates charge separation^[20]. Chen et al. made facile NiO_x modification by KCl to synchronously suppress interfacial recombination and ion migration^[21].

The interfacial recombination loss and mismatched band alignment limit the performance enhancement of inverted PSCs. Though doping metal cations could improve the conductivity of NiO_x layer, the impurity ions cannot be avoided. In response, Wang et al. used [BMIm]BF₄ ionic liquid (IL) assisted synthesis to prepare high-quality NiO_x nanoparticles^[22]. $[BMIm]BF_4$ is added before the reaction of Ni(NO₃)₂ with NaOH (Fig. 2(b)). The multifunctional substitution of imidazole rings produces more chemical bonds. In addition, cations can inhibit the adsorption of impurity ions on Ni(OH)₂, thus obtaining NiO_x-IL HTL with high conductivity. Yang et al. used TTTS as a chelating agent of Ni²⁺ in NiO_x layer to improve its conductivity^[23]. TTTS and Ni²⁺ are combined by strong Ni²⁺–N coordination bonds in NiO_x, increasing the ratio of Ni^{3+} : Ni^{2+} (Fig. 2(c)). The increase of Ni^{3+} content adjusted the band structure of NiOx, thereby increasing the hole density and mobility, resulting in enhanced PCE over 22%. Carbon materials with good conductivity are also suitable modifiers for NiOx. Yin et al. developed a NiOx/carbon heterostructure (Fig. 2(d)) as an interlayer for fabricating efficient PSCs with good interfacial energy level alignment and more efficient charge transport^[24].

The interfacial lattice mismatch and adverse reactions in NiO_x-based PSCs cannot be ignored. Self-assembled molecu-

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Fig. 1. (Color online) (a) Sol-gel preparation of NiO_x nanoparticles. Reproduced with permission^[8], Copyright 2023, Wiley. (b) Possible degradation mechanism of NiO_x -perovskite heterojunction. Reproduced with permission^[10], Copyright 2022, the Royal Society of Chemistry.



Fig. 2. (Color online) (a) The oxidation state and ionic radius for several metals. Reproduced with permission^[19], Copyright 2020, the Royal Society of Chemistry. (b) Synthesis of NiO_x nanoparticles. Reproduced with permission^[22], Copyright 2022, Wiley. (c) NiO_x modified by TTTS. Reproduced with permission^[23], Copyright 2022, Wiley. (d) The preparation of NiO_x/carbon heterostructure. Reproduced with permission^[24], Copyright 2021, Wiley. (e) SAM-modified NiO_x at the interface. Reproduced with permission^[27], Copyright 2021, Wiley. (f) Flexible PSCs with bridging molecules. Reproduced with permission^[28], Copyright 2022, Nature. (g) The energy level diagram for device with PTAA. Reproduced with permission^[30], Copyright 2021, Elsevier. (h) TMSBr buffer layer inhibiting perovskite degradation. Reproduced with permission^[10], Copyright 2022, the Royal Society of Chemistry.

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lar layers (SAMLs) are effective carrier-transport layers in PSCs due to their unique ability to manipulate interface properties as well as their simple processing and scalable manufacturing^[25]. However, the defects and pinholes caused by its adsorption process can seriously degrade device performance. Therefore, SAMLs are often combined with hole-transport materials such as NiO_x to improve hole transport. The phosphoric acid (PA) group in 2PACz has a strong coordination with $NiO_{x}^{[26]}$, and it is easier to spin-coat 2PACz onto NiO_{x} layer. The presence of 2PACz can promote the crystallization of perovskite and regulate the bandgap of perovskite. Sun et al. found that tridentate binding between MeO-2PACz and NiOx is superior to the double-toothed binding between MeO-2PACz and ITO (Fig. 2(e))^[27]. This close contact reduces defects and pinholes at the interface, thereby improving device performance. In 2022, Li et al. used a mixture of 2PACz and MeO-2PACz as a molecular bridge at the interface to reduce interface recombination and they can act as a stress buffer layer at the interface to improve the bending durability of the flexible device (Fig. 2(f))^[28]. Recently, Zhang et al. used p-chlorobenzenesulfonic acid (CBSA) self-assembly to anchor NiO_x and perovskite crystals, where the chlorine end can provide a growth site for perovskite and also release the interfacial strain^[29]. The sulfonic acid group in CBSA can passivate the surface defects of $\ensuremath{\text{NiO}_{x\prime}}$ which is conducive to carrier extraction.

Besides SAMLs, introducing long-chain organic molecules can also improve surface properties for bandgap alignment and charge transfer. PTAA can act as a molecular bridge. Fig. 2(g) shows that the valence band of PTAA (–5.2 eV) is very close to the valence band of NiO_x (–5.1 eV) and perovskite (–5.3 eV), which can quickly transfer holes from perovskite to NiO_x^[30]. Recently, Li *et al.* obtained a PCE of 25.12% (certified 24.6%) for inverted NiO_x-based PSCs by using NiO_x/PTAA/Al₂O₃ as hole-transport layer^[31]. To eliminate multistep photochemical reactions at the interface, Wu *et al.* constructed an aprotic trimethyl bromosulfonic acid (TMSBr) buffer layer at NiO_x/perovskite interface (Fig. 2(h))^[10]. TMSBr has excellent photothermal stability, and strong trap-passivation capability. The T₈₀ lifetime for the device under AM1.5G light is 2310 h.

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